Munetaka Noguchi

List of Publications by Year
in descending order

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8 papers	82 citations	1684188 5 h-index	1720034 7 g-index
8 all docs	8 docs citations	8 times ranked	61 citing authors

#	Article	IF	Citations
1	Carrier transport properties in inversion layer of Si-face 4Hâ€“SiC MOSFET with nitrided oxide. Japanese Journal of Applied Physics, 2019, 58, 031004.	1.5	33
2	Hall effect mobility for SiC MOSFETs with increasing dose of nitrogen implantation into channel region. Japanese Journal of Applied Physics, 2018, 57, 04FR13.	1.5	12
3	Coulomb-limited mobility in 4H-SiC MOS inversion layer as a function of inversion-carrier average distance from MOS interface. Japanese Journal of Applied Physics, 2020, 59, 051006.	1.5	12
4	Hall effect mobility in inversion layer of 4H-SiC MOSFETs with a thermally grown gate oxide. Japanese Journal of Applied Physics, 2019, 58, SBBD14.	1.5	10
5	Comparative Study of Hall Effect Mobility in Inversion Layer of 4H-SiC MOSFETs With Nitrided and Phosphorus-Doped Gate Oxides. IEEE Transactions on Electron Devices, 2021, 68, 6321-6329.	3.0	8
6	Compatibility of POCl₃ Gate Process with the Fabrication of Vertical 4H-SiC MOSFETs. Materials Science Forum, 0, 1004, 565-570.	0.3	3
7	Flat-band voltage shift of 4H-SiC MOS capacitors induced by interface dipole layer formation at the oxide-semiconductor and oxide-oxide interfaces. Solid-State Electronics, 2021, 183, 108115.	1.4	2
8	Impacts of Al₂O₃/SiO₂ Interface Dipole Layer Formation on the Electrical Characteristics of 4H-SiC MOSFET. IEEE Electron Device Letters, 2022, 43, 92-95.	3.9	2